

# isc N-Channel MOSFET Transistor

# **IXKC19N60C5**

#### FEATURES

- · High power dissipation
- Static drain-source on-resistance: R<sub>DS</sub>(on) ≤ 125mΩ@V<sub>GS</sub>=10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATION

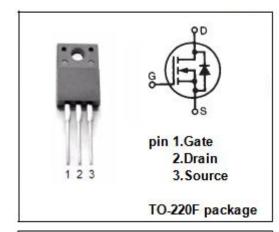
- DC/DC Converters
- High Current Switching Applications

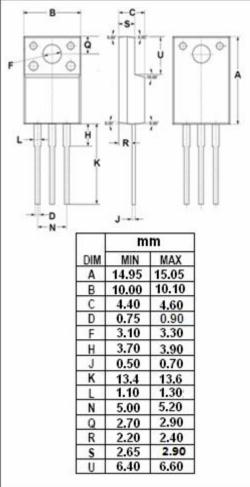


SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	600	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	19	А
Ірм	Drain Current-Single Pulsed	15	А
Tj	Operating Junction Temperature	-55~150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th(j-c)</sub>	Junction-to-case thermal resistance	0.95	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID = 250 μ A	600			V
Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID = 100 μ A	2.5		3.5	V
Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 16A			125	mΩ
Gate-Source Leakage Current	$V_{GS}$ = ±20V; $V_{DS}$ =0V			±100	nA
Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V:T <sub>I</sub> = 125°C		20	2	μ <b>А</b>
Diode forward voltage	I <sub>F</sub> = 16A; V <sub>GS</sub> = 0V			1.2	V
	Drain-Source Breakdown Voltage  Gate Threshold Voltage  Drain-Source On-Resistance  Gate-Source Leakage Current  Drain-Source Leakage Current	Drain-Source Breakdown Voltage $V_{GS}=0V;\ ID=250\ \mu\ A$ Gate Threshold Voltage $V_{DS}=V_{GS};\ ID=100\ \mu\ A$ Drain-Source On-Resistance $V_{GS}=10V;\ I_{D}=16A$ Gate-Source Leakage Current $V_{DS}=V_{DSS};\ V_{GS}=0V$ Drain-Source Leakage Current $V_{DS}=V_{DSS};\ V_{GS}=0V$	Drain-Source Breakdown Voltage $V_{GS}=0V;\ ID=250\ \mu\ A$ 600  Gate Threshold Voltage $V_{DS}=V_{GS};\ ID=100\ \mu\ A$ 2.5  Drain-Source On-Resistance $V_{GS}=10V;\ I_{D}=16A$ Gate-Source Leakage Current $V_{DS}=V_{DSS};\ V_{GS}=0V$ Drain-Source Leakage Current $V_{DS}=V_{DSS};\ V_{GS}=0V$	Drain-Source Breakdown Voltage $V_{GS}=0V$ ; $ID=250~\mu$ A 600  Gate Threshold Voltage $V_{DS}=V_{GS}$ ; $ID=100~\mu$ A 2.5  Drain-Source On-Resistance $V_{GS}=10V$ ; $I_{D}=16A$ Gate-Source Leakage Current $V_{DS}=\pm 20V$ ; $V_{DS}=0V$ Drain-Source Leakage Current $V_{DS}=V_{DSS}$ ; $V_{GS}=0V$ $V_{DS}=V_{DSS}$ ; $V_{GS}=0V$ ; $V_{DS}=0V$	Drain-Source Breakdown Voltage $V_{GS}=0V$ ; $ID=250~\muA$ 600  Gate Threshold Voltage $V_{DS}=V_{GS}$ ; $ID=100~\muA$ 2.5 3.5  Drain-Source On-Resistance $V_{GS}=10V$ ; $I_{D}=16A$ 125  Gate-Source Leakage Current $V_{GS}=\pm20V$ ; $V_{DS}=0V$ $\pm100$ Drain-Source Leakage Current $V_{DS}=V_{DSS}$ ; $V_{GS}=0V$ 2 $V_{DS}=V_{DSS}$ ; $V_{GS}=0V$ ; $V_{DS}=125$ °C 20

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